編號: 214、215、>>8 國立成功大學九十八學年度碩士班招生考試試題 共 3 頁,第/頁

系所組別: 電機工程學系甲、乙、丁、戊組**,微電子工程研究所,電腦與通信工程研究所丙、丁**組

考試科目: 電子學 考試日期: 0307,節次: 1

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- A full-wave rectifier circuit shown in Fig. 1 is to deliver 0.1 A and 15 V (average) to a load R. The ripple voltage is to be no larger than 0.4 V peak-to-peak. The input signal V<sub>I</sub> is 120 V (rms) at 60 Hz. Assume diode turn-on voltages of 0.7 V. Determine the required turns ratio (N<sub>1</sub>/N<sub>2</sub>) and the filter capacitance C value. (11%)
- 2. A CMOS inverter circuit shown in Fig. 2 has the parameters of  $V_{DD}$ =5 V,  $V_{TN}$ =- $V_{TP}$ =1 V,  $K_N$ =100  $\mu$ A/V<sup>2</sup>, and  $K_P$ =50  $\mu$ A/V<sup>2</sup>. Determine the values of noise margins (NM<sub>L</sub>, NM<sub>H</sub>) and the gate threshold voltage V<sub>M</sub>. (22%)
- 3. (a) Explain briefly why BJTs and FETs can amplify ac signals? (6%)
  - (b) Redefine the small-signal parameters of the transistor to absorb the emitter resistance  $R_E$  in Fig. 3 (i.e., to find  $g_{m2}$ ,  $r_{\pi 2}$ , and  $r_{o2}$  in terms of  $g_{m1}$ ,  $r_{\pi 1}$ , and  $r_{o1}$ ). (6%)
  - (c) A single BJT amplifier is needed that has a gain of  $\sim 0$  dB and an input resistance of 25 M $\Omega$  with a load resistance of 25 k $\Omega$ . What is the preferred choice of amplifier configuration? Explain why you made this selection. (4%)
- 4. (a) Derive  $i_{out}$  and  $R_{out}$  for the circuit shown in Fig. 4. Assume the small-signal parameters of the MOSFET are  $g_m$  and  $r_o$ . (8%)
  - (b) The MOSFETs in the circuit of Fig. 5 are matched, having  $k_n'(W/L)_1 = k_p'(W/L)_2 = 1.5 \text{ mA/V}^2$  and  $|V_t| = 0.5 \text{ V}$ . For G and D open, find the drain currents  $I_{DI}$  and  $I_{D2}$ . For  $r_o = \infty$ , what is the voltage gain of the amplifier from G to D? (10%)

(背面仍有題目,請繼續作答)

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5. Consider the circuit as shown in Fig. 6. The circuit is biased with  $V_{cc} = 12 \text{ V}$ , and the load resistance is  $R_L = 75 \Omega$ .

The device parameters are:

$$I_{SD} = 5 \times 10^{-13} \text{ A for } D_1 \text{ and } D_2,$$

$$I_{SQ}\!=2\!\times\!10^{\text{--}13}\,A$$
 ,  $\beta_{n}\!=\beta_{p}\!=60$  for  $Q_{n}$  and  $Q_{p}.$ 

- (a) Neglecting base currents, determine the required value of  $I_{Bias}$  such that the quiescent currents in  $Q_n$  and  $Q_p$  are  $I_{CQ} = 5$  mA. (6%)
- (b) Find  $i_{cn}$ ,  $i_{cp}$ ,  $V_{BEn}$ ,  $V_{EBp}$ , and  $I_D$  when  $V_0=2$  V. (8 %)
- (c) What is the power conversion efficiency for this circuit when the output is a sinusoid and the peak output voltage reaches 80 percent of  $V_{cc}$ ? (8%)
- 6. Consider the phase-shift oscillator shown in Fig. 7, with parameters C = 100 pF and  $R = 10 \text{ K}\Omega$ .
  - (a) Determine the frequency of oscillation. (6%)
  - (b) Find the minimum required value of R<sub>2</sub> for sustaining oscillation. (5%)

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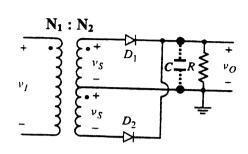


Fig. 1

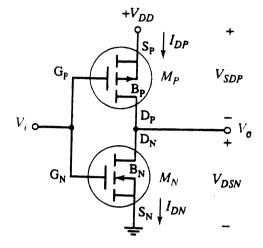


Fig. 2

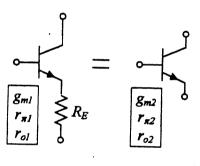


Fig. 3

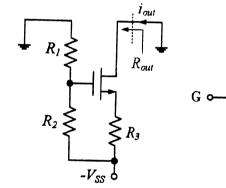


Fig. 4

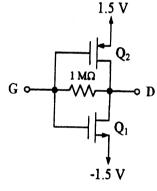
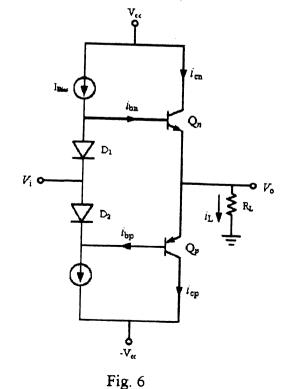


Fig. 5



 $\begin{bmatrix} C & C & C & R & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & \\ & & & \\ & & \\ & & & \\ & & & \\ & & \\ & & & \\ & & & \\ & & & \\ &$ 

Fig. 7